## Silicon N-Channel MOS FET

# **HITACHI**

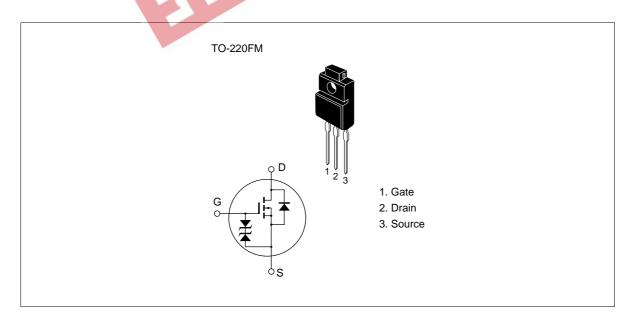
### **Application**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Tom.cn Suitable for switching regulator and DC-DC converter

#### **Outline**





### **Absolute Maximum Ratings** (Ta = 25°C)

Item		Symbol	Ratings	Unit	
Drain to source voltage	2SK1566	V <sub>DSS</sub>	450	V	
	2SK1567		500		
Gate to source voltage		$V_{\sf GSS}$	±30	V	
Drain current	I <sub>D</sub>	7	А		
Drain peak current	I <sub>D(pulse)</sub> *1	28	А		
Body to drain diode reverse	I <sub>DR</sub>	7	А		
Channel dissipation	Pch*2	35	W		
Channel temperature	Tch	150	°C		
Storage temperature		Tstg	-55 to +150	°C	
		N.S.	-55 (0 +150		

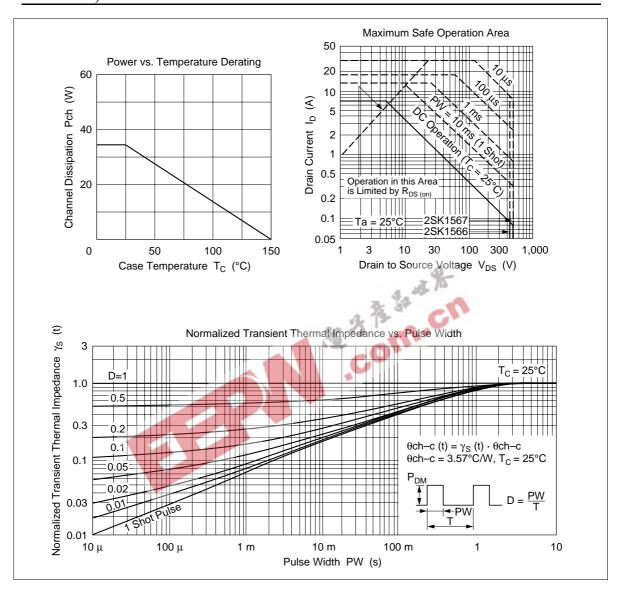


## **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

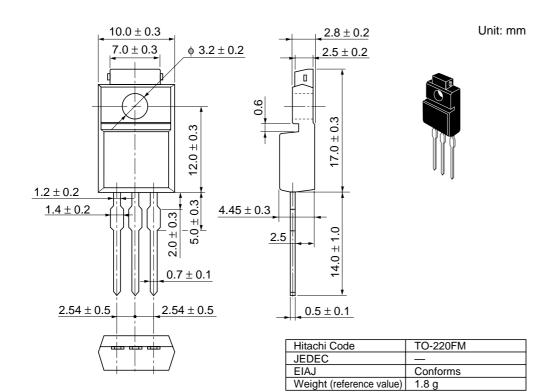
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1566	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage	2SK1567	-	500	_			
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage	2SK1566	I <sub>DSS</sub>	_	_	250	μΑ	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
drain current	2SK1567	-					$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff	voltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source	2SK1566	R <sub>DS(on)</sub>	_	0.6	0.8	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
on state resistance	2SK1567		_	0.7	0.9	4	
Forward transfer adm	ittance	yfs	4.0	6.5	_	S	$I_D = 4 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		Ciss	_	1050	一卷	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss	_	280	25	pF	f = 1 MHz
Reverse transfer capa	acitance	Crss	- \	40	7.0	pF	-
Turn-on delay time		t <sub>d(on)</sub>	$\pm 10$	15	-	ns	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time		tr	<del>-)</del> ,	55	_	ns	$R_L = 7.5 \Omega$
Turn-off delay time		t <sub>d(off)</sub>		95	_	ns	-
Fall time	1	t <sub>f</sub>	_	40	_	ns	-
Body to drain diode for voltage	orward	V <sub>DF</sub>	_	0.95	_	V	$I_F = 7 \text{ A}, V_{GS} = 0$
Body to drain diode re recovery time	everse	t <sub>rr</sub>	_	320	_	ns	$I_F = 7 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note 1. Pulse test

See characteristic curves of 2SK1157, 2SK1158.







#### **Cautions**

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as failsafes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109 URI

NorthAmerica http:semiconductor.hitachi.com/ http://www.hitachi-eu.com/hel/ecg Europe

http://www.has.hitachi.com.sg/grp3/sicd/index.htm http://www.hitachi.com.tw/E/Product/SICD\_Frame.htm Asia (Singapore) Asia (Taiwan) Asia (HongKong) http://www.hitachi.com.hk/eng/bo/grp3/index.htm

Japan http://www.hitachi.co.jp/Sicd/indx.htm

#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group.

Whitebrook Park

Lower Cookham Road

Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd

Taipei Branch Office 3F, Hung Kuo Building. No.167 Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.